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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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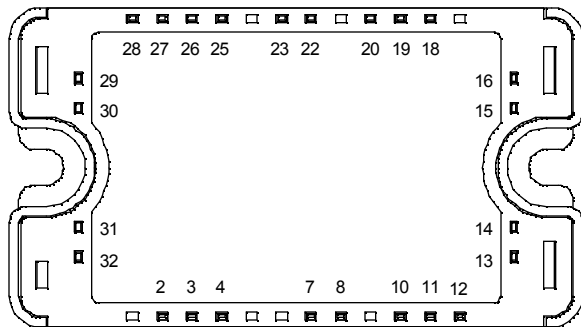
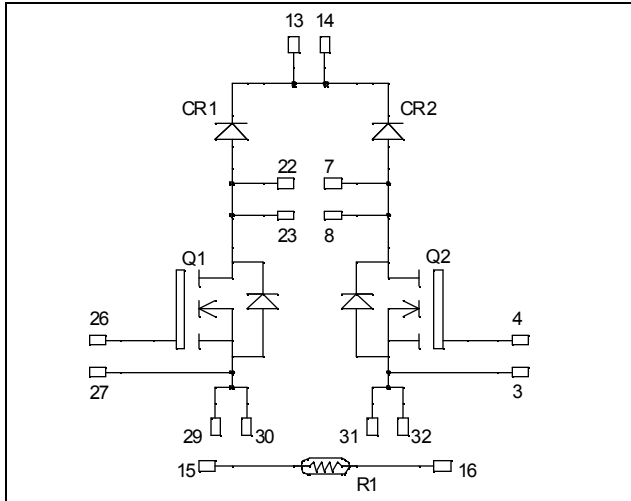
Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



Dual boost chopper Super Junction MOSFET Power Module

$V_{DSS} = 600V$
 $R_{DSon} = 70m\Omega \text{ max @ } T_j = 25^\circ C$
 $I_D = 39A \text{ @ } T_c = 25^\circ C$



All multiple inputs and outputs must be shorted together
 Example: 13/14 ; 29/30 ; 22/23 ...

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- **COOLMOS** Power Semiconductors
 - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a single boost of twice the current capability
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	600	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	39
		$T_c = 80^\circ C$	29
I_{DM}	Pulsed Drain current	160	
V_{GS}	Gate - Source Voltage	± 20	V
R_{DSon}	Drain - Source ON Resistance	70	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	250
I_{AR}	Avalanche current (repetitive and non repetitive)	20	A
E_{AR}	Repetitive Avalanche Energy	1	mJ
E_{AS}	Single Pulse Avalanche Energy	1800	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{V}, V_{DS} = 600\text{V}$			25	μA
		$V_{GS} = 0\text{V}, V_{DS} = 600\text{V}$			250	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 39\text{A}$			70	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.7\text{mA}$	2.1	3	3.9	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$		7		nF
C_{oss}	Output Capacitance	$V_{DS} = 25\text{V}$		2.56		
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.21		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$		259		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 300\text{V}$		29		
Q_{gd}	Gate – Drain Charge	$I_D = 39\text{A}$		111		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching @ 125°C $V_{GS} = 15\text{V}$ $V_{Bus} = 400\text{V}$ $I_D = 39\text{A}$ $R_G = 5\Omega$		21		ns
T_r	Rise Time			30		
$T_{d(off)}$	Turn-off Delay Time			283		
T_f	Fall Time			84		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15\text{V}, V_{Bus} = 400\text{V}$ $I_D = 39\text{A}, R_G = 5\Omega$		670		μJ
E_{off}	Turn-off Switching Energy			980		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15\text{V}, V_{Bus} = 400\text{V}$ $I_D = 39\text{A}, R_G = 5\Omega$		1096		μJ
E_{off}	Turn-off Switching Energy			1206		

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 600\text{V}$	$T_j = 25^\circ\text{C}$		250	μA
			$T_j = 125^\circ\text{C}$		500	
I_F	DC Forward Current			40		A
V_F	Diode Forward Voltage	$I_F = 40\text{A}$ $V_{GE} = 0\text{V}$	$T_j = 25^\circ\text{C}$		1.45	V
			$T_j = 125^\circ\text{C}$		1.35	
t_{rr}	Reverse Recovery Time	$I_F = 40\text{A}$ $V_R = 300\text{V}$	$T_j = 25^\circ\text{C}$		95	ns
			$T_j = 125^\circ\text{C}$		115	
Q_{rr}	Reverse Recovery Charge	$di/dt = 2600\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		2.6	μC
			$T_j = 125^\circ\text{C}$		4	

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance	Transistor		0.5	°C/W	
		Diode		1.5		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz	2500			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				110	g

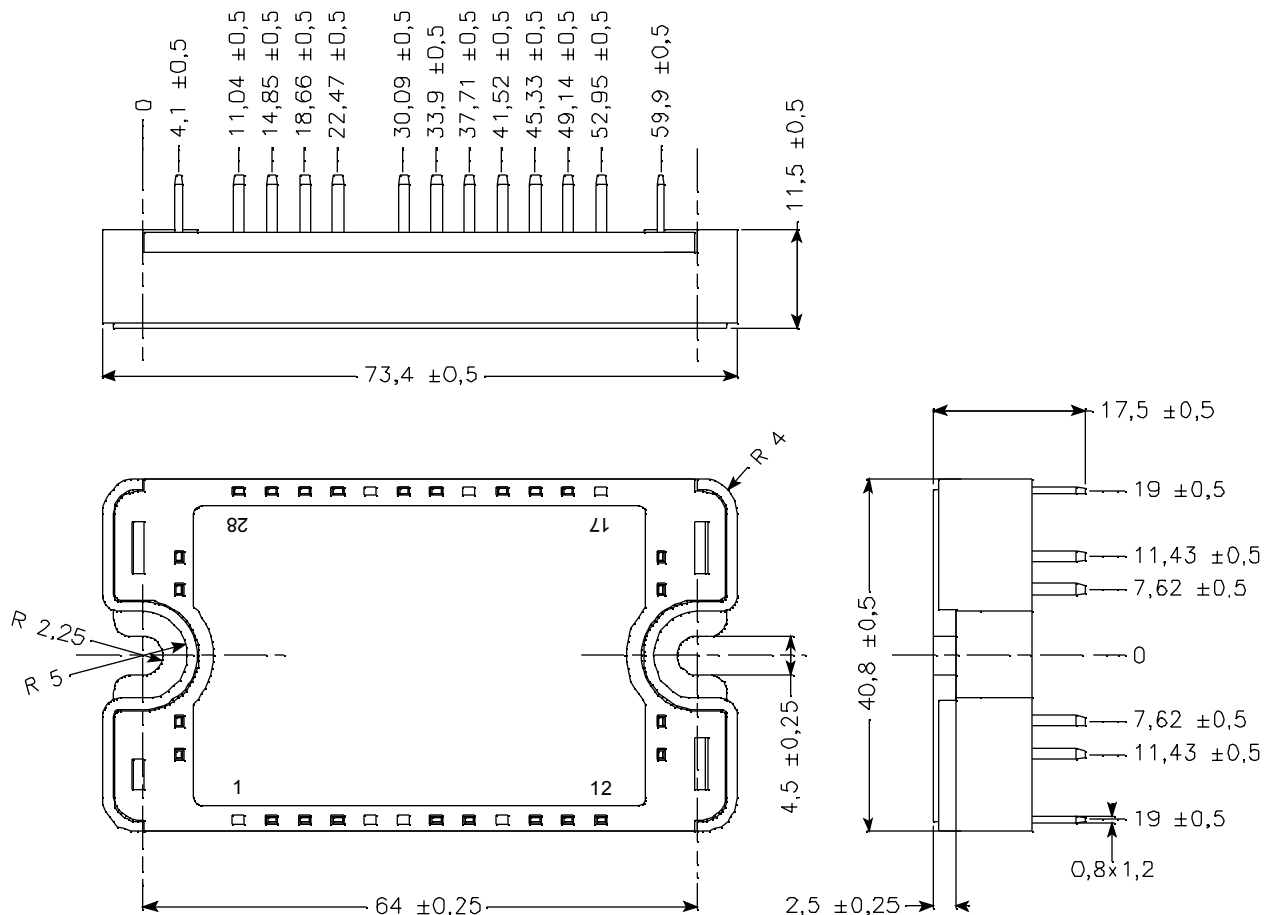
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

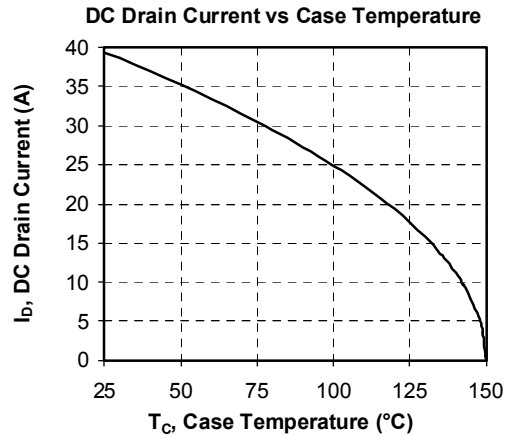
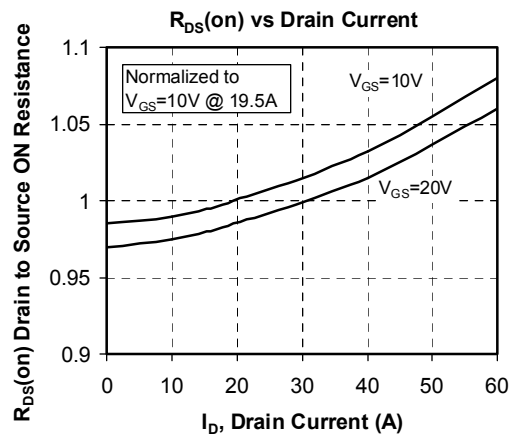
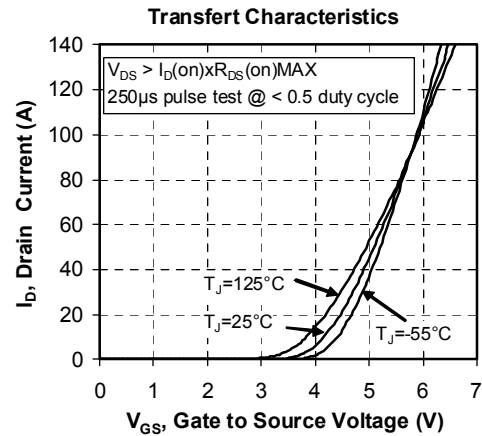
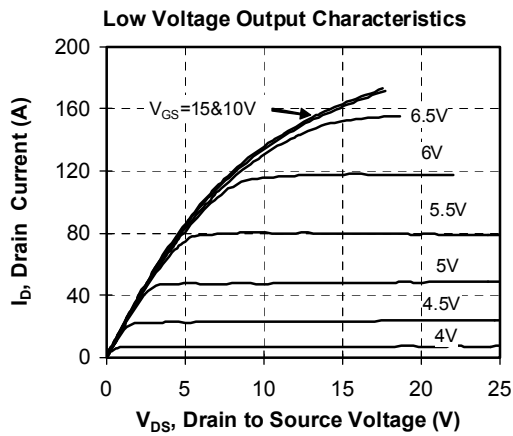
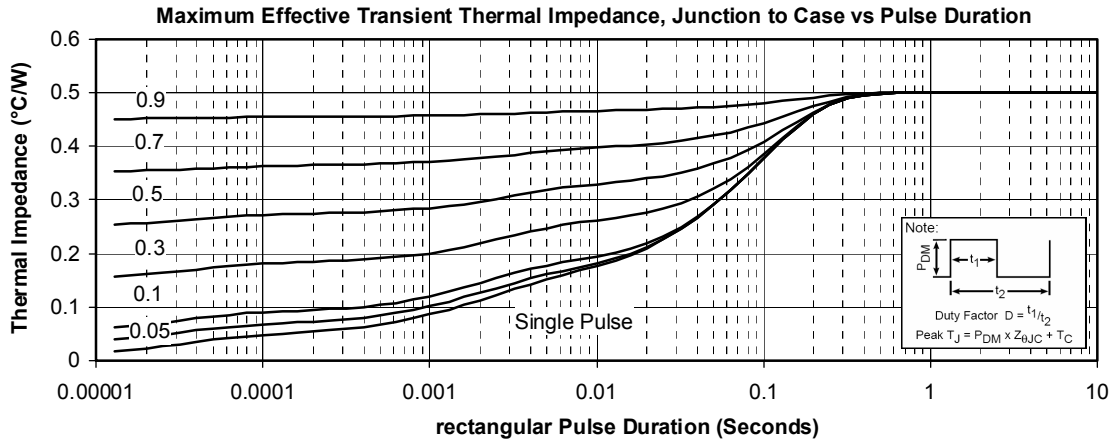
T: Thermistor temperature
 R_T: Thermistor value at T

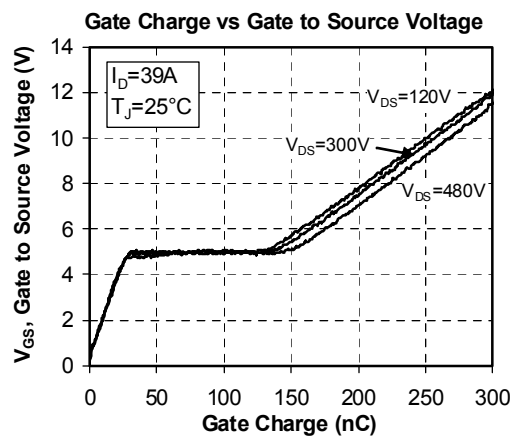
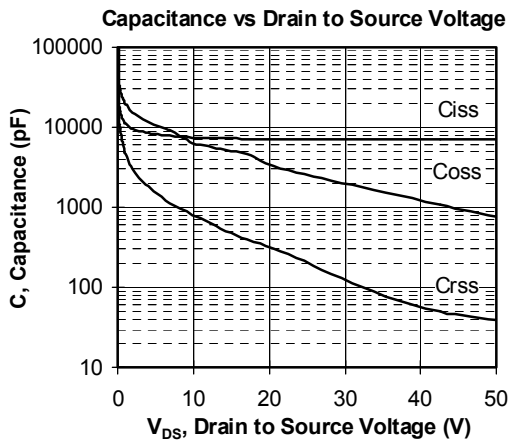
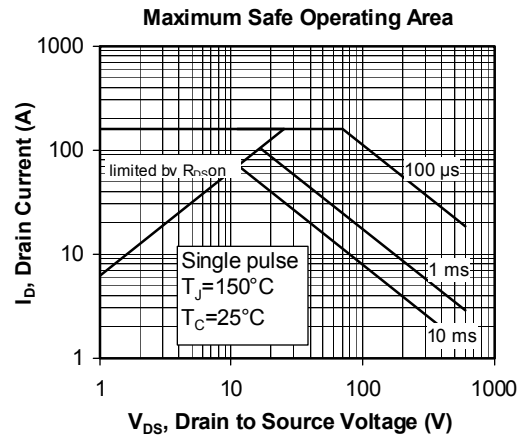
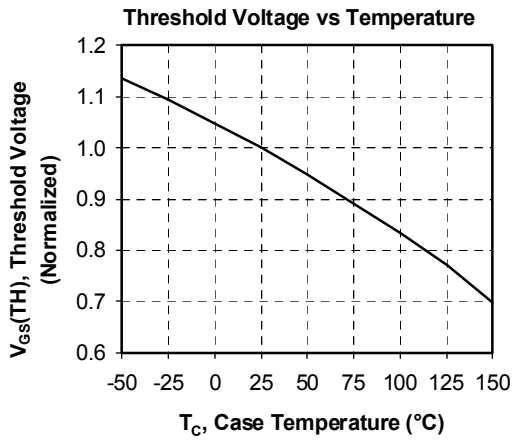
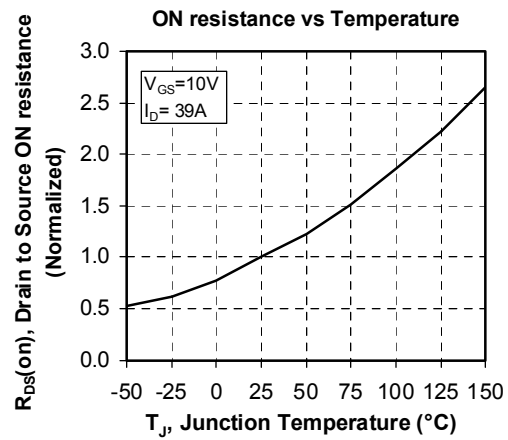
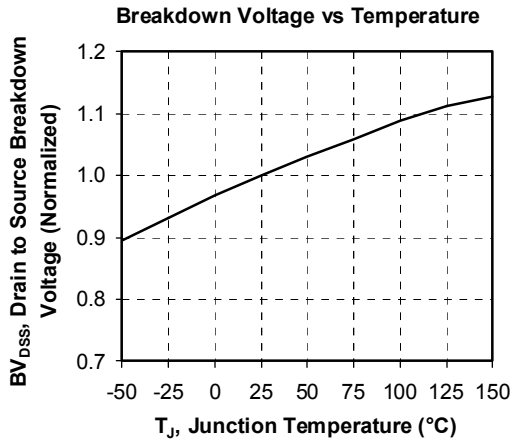
SP3 Package outline (dimensions in mm)

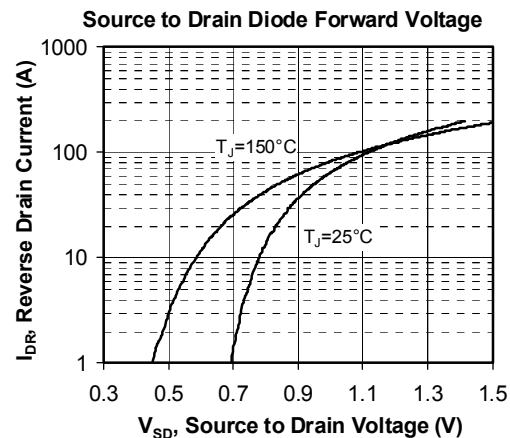
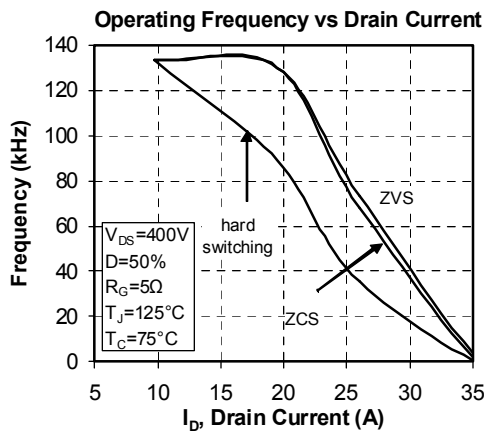
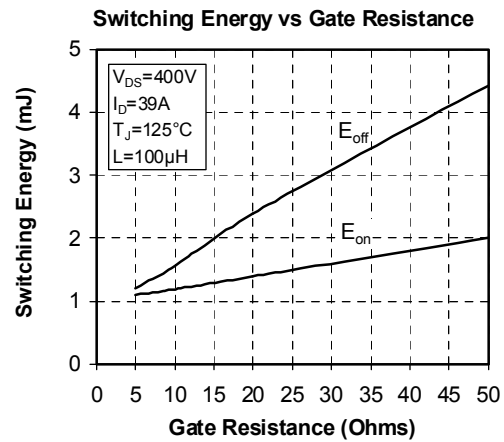
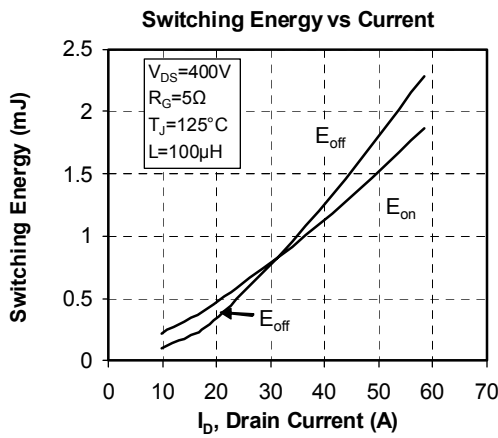
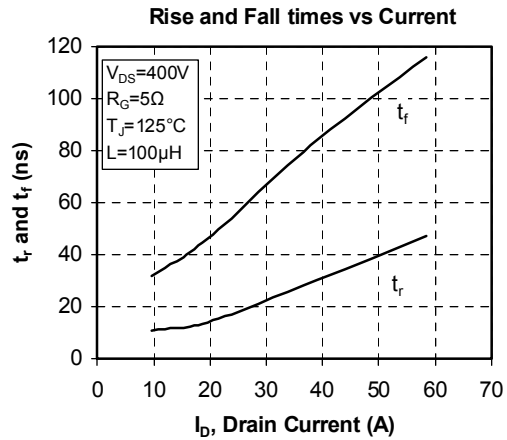
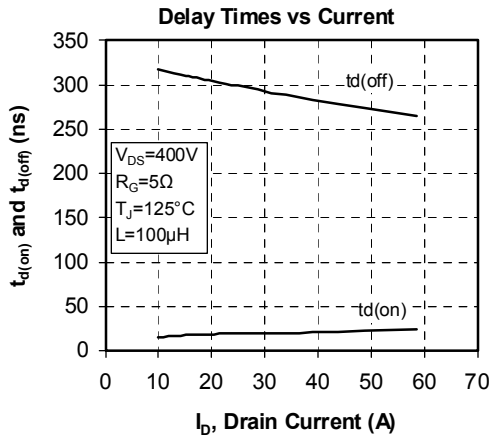


See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Typical Performance Curve







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Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.